

# *Monolithic Bi-Directional Switches — X-Technology of 3- $\Phi$ AC/DC Mains Interfaces*

**Johann W. Kolar et al.**



Swiss Federal Institute of Technology (ETH) Zurich  
Power Electronic Systems Laboratory  
[www.pes.ee.ethz.ch](http://www.pes.ee.ethz.ch)

*Special  
Session*

Wide-Bandgap  
Bidirectional Switches  
and the Applications  
They Enable

*Oct. 10, 2021*



# *M-BDS — X-Technology of 3- $\Phi$ AC/DC Mains Interfaces*

Johann W. Kolar | **Jonas E. Huber** | **F. Vollmaier** | **Daifei Zhang** | **Neha Nain**



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## Outline



- ▶ *Introduction*
- ▶ *Integrated Active Filter PFC Concepts*
- ▶ *3-Level T-Type Boost Converters*
- ▶ *Current Source Buck-Boost Converters*
- ▶ *Isolated Matrix-Type Converters*
- ▶ *Conclusions*

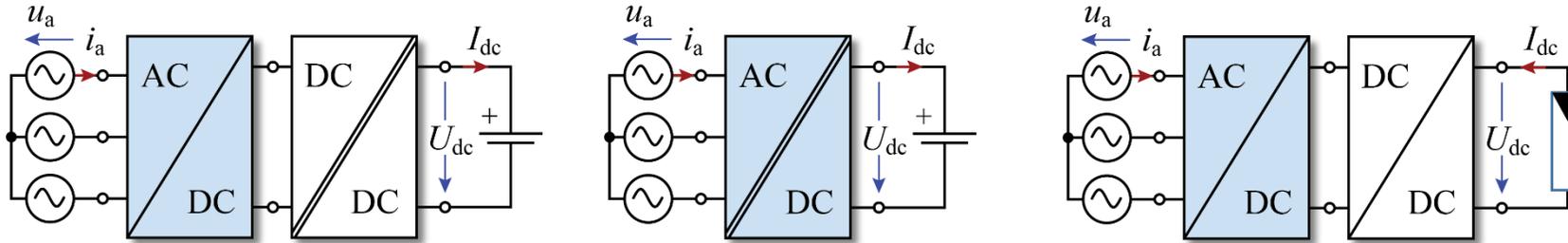
Acknowledgement

F. Krismer

# 3- $\Phi$ AC/DC Converter Application Areas

- *Electric Vehicle Battery Charging*
- *Datacenter Power Supply*
- *Renewable Energy Applications*

Typ. 200...1000V<sub>DC</sub> EV Battery Voltage Range



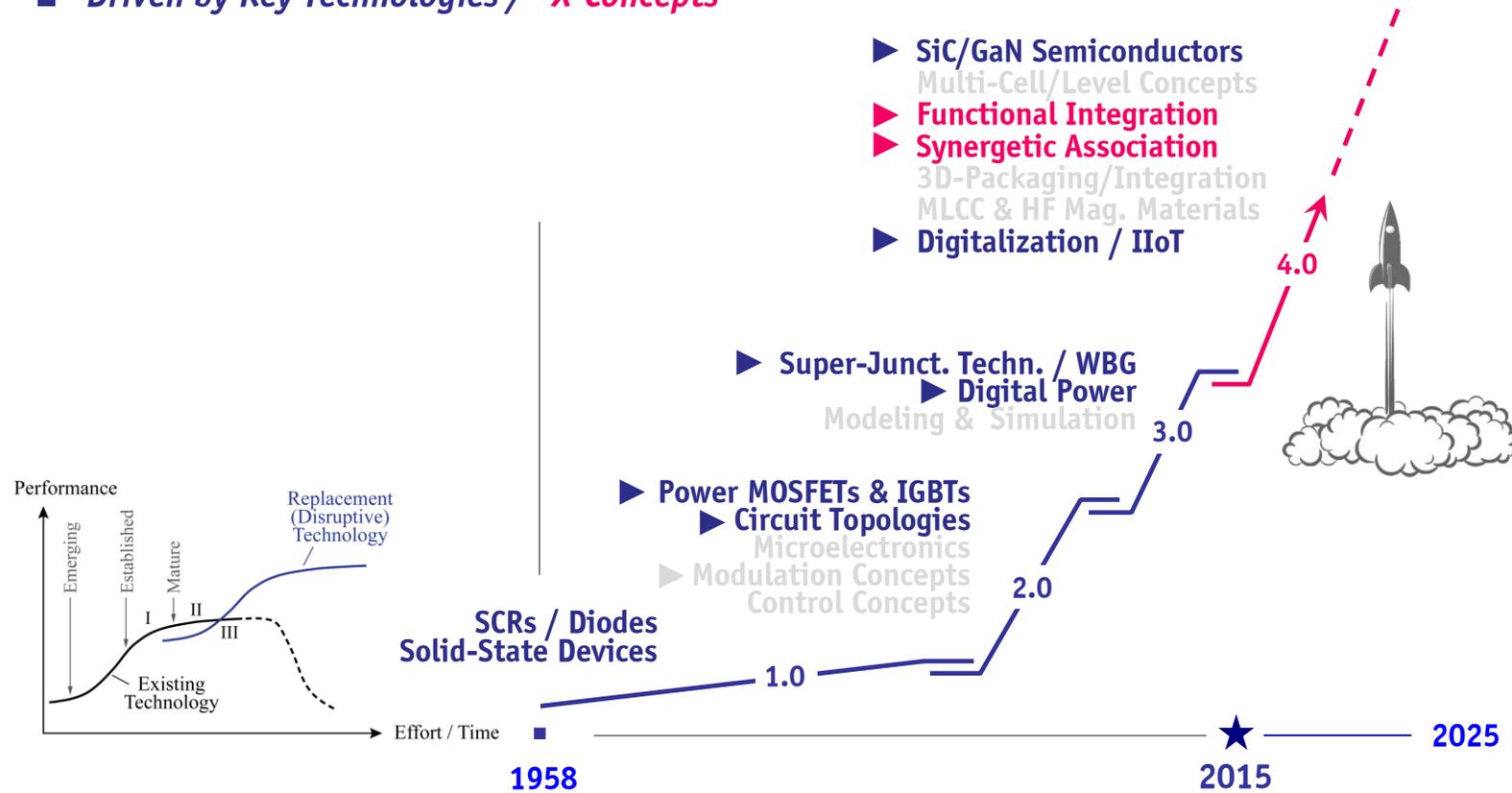
320...530V<sub>rms</sub> Line-to-Line

MPP Tracking in 60...90% of Max. Open Circuit Voltage

- *Non-Isolated* OR *Isolated Output*
- *Wide AC Input* &/OR *DC Output Voltage Range*
- *Unidirectional* OR *Bidirectional Power Transfer*

# S-Curve of Power Electronics

- *Power Electronics 1.0* → *Power Electronics 4.0*
- *Driven by Key Technologies / "X-Concepts"*

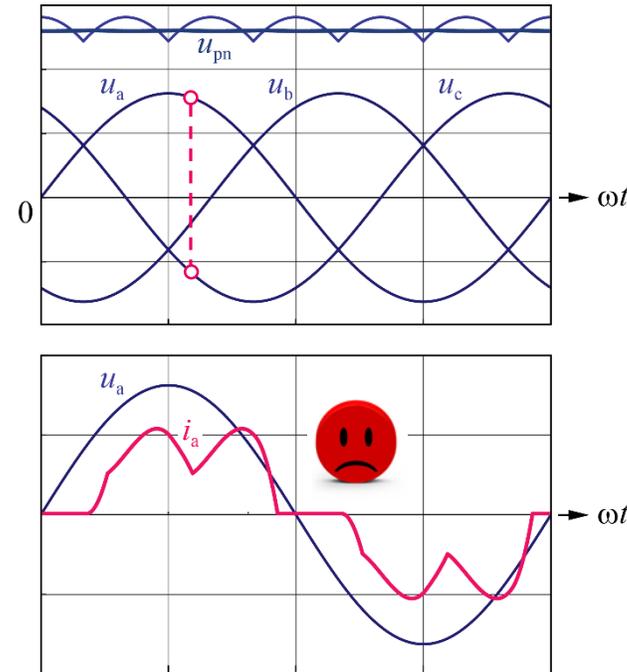
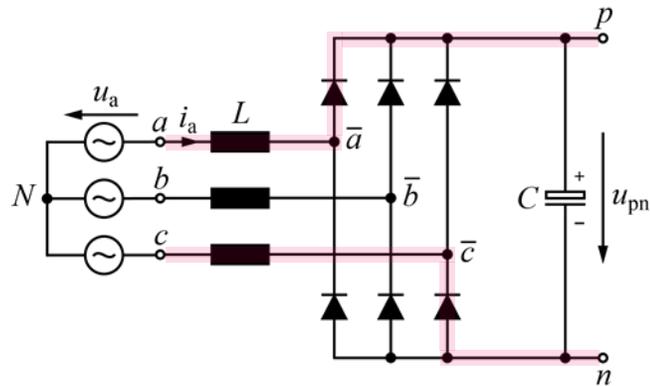




———— *3<sup>rd</sup> Harmonic Injection* ————  
*PFC Rectifier*

# 3- $\Phi$ Diode Bridge Rectifier

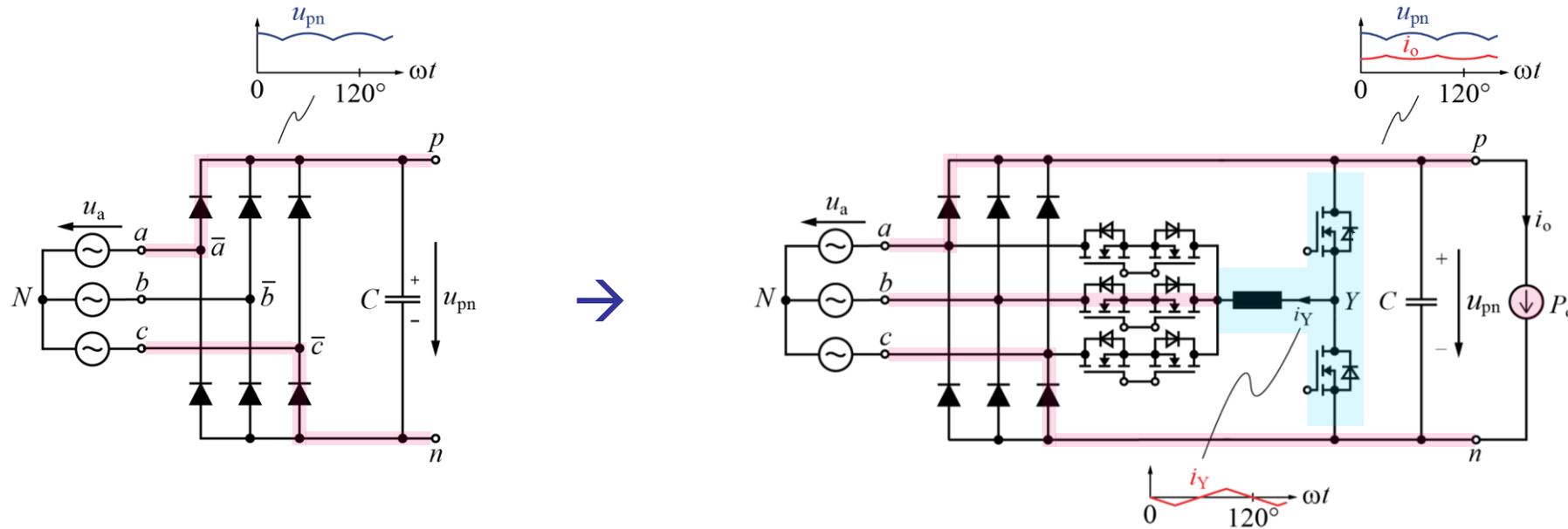
- *Conduction States Defined by Line-to-Line Mains Voltages*
- *Intervals with Zero Current / LF Harmonics*
- *No Output Voltage Control*



→ *Active Mains Current Shaping / Simultaneous Current Flow in All Phases*

# Integrated Active Filter (IAF) PFC Rectifier

- **3<sup>rd</sup> Harmonic Current Injection** into Phase with Lowest Voltage
- **Phase Selector AC Switches** Operated @ Mains Frequency — **3- $\Phi$  Unfolder**



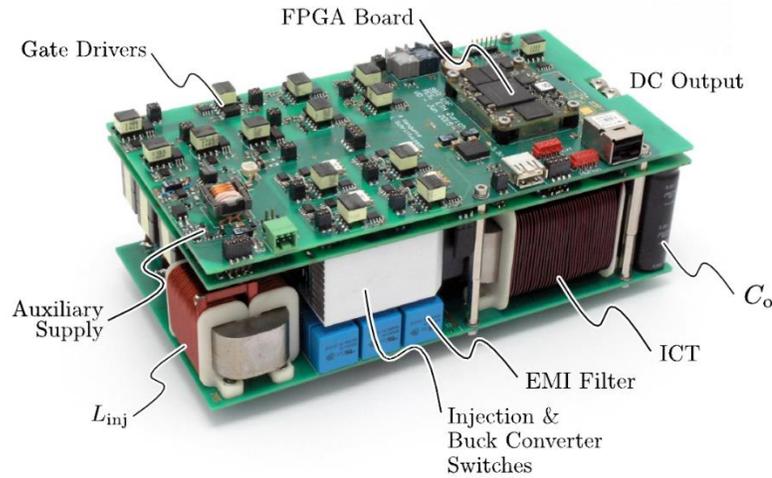
- **Non-Sinusoidal Mains Current**

- $P_o = \text{const. Required}$
- **Sinusoidal Mains Current**
- **NO (!) DC Voltage Control**

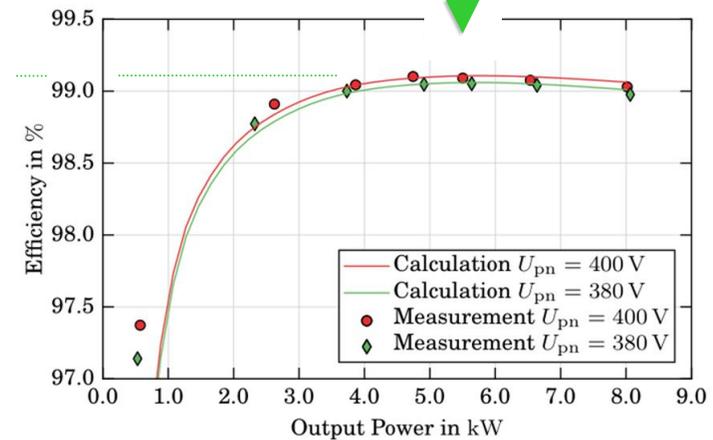
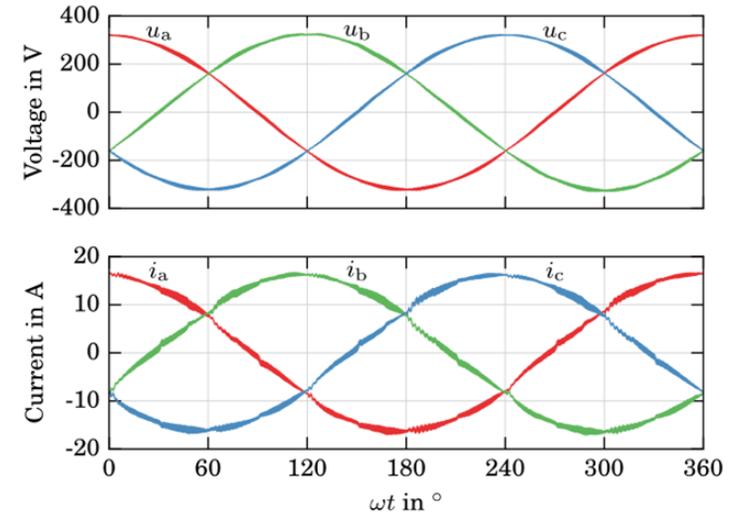
# IAF Rectifier Demonstrator

- Efficiency  $\eta > 99.1\%$  @ 60% Rated Load
- Mains Current  $THD_I \approx 2\%$  @ Rated Load
- Power Density  $\rho \approx 4\text{kW}/\text{dm}^3$

$P_o = 8\text{ kW}$   
 $U_N = 400\text{V}_{AC} \rightarrow U_o = 400\text{V}_{DC}$   
 $f_s = 27\text{kHz}$

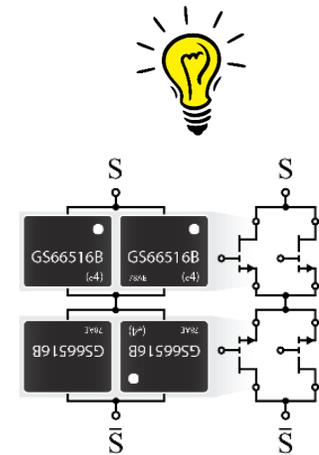
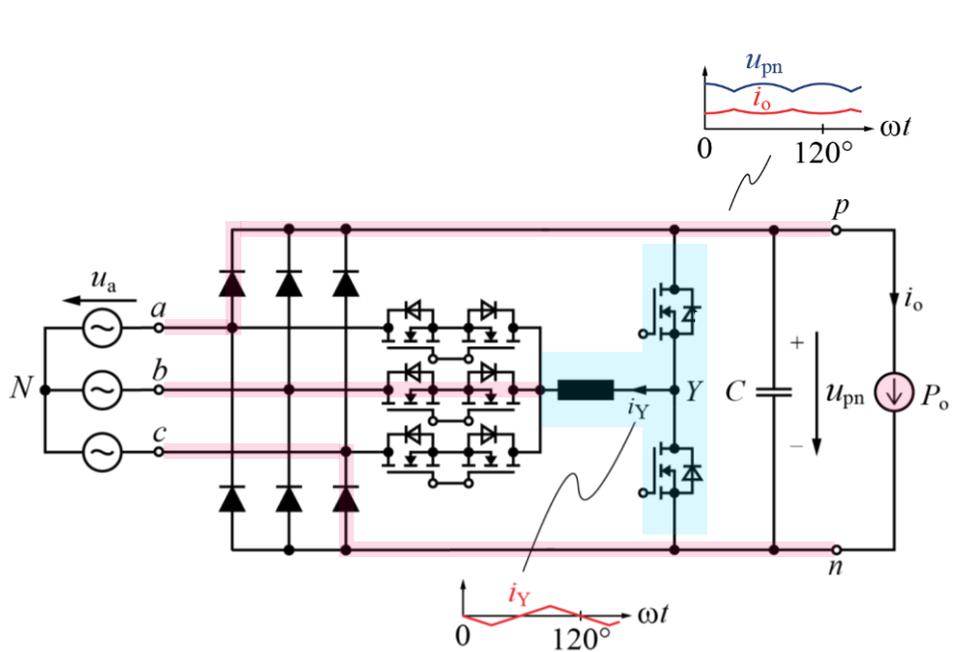


- SiC Power MOSFETs & Diodes
- 2 Interleaved Buck Output Stages

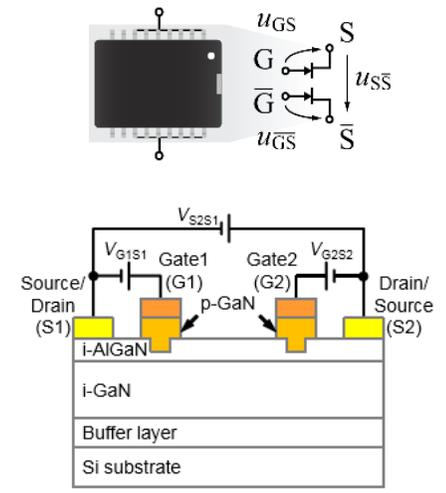


# Remark Application of GaN M-BDS (1)

- Realization of the **Phase Selector Switches** of 3<sup>rd</sup> Harmonic Inj. PFC Rectifiers
- **Bipolar Voltage Blocking / Current Carrying Capability**



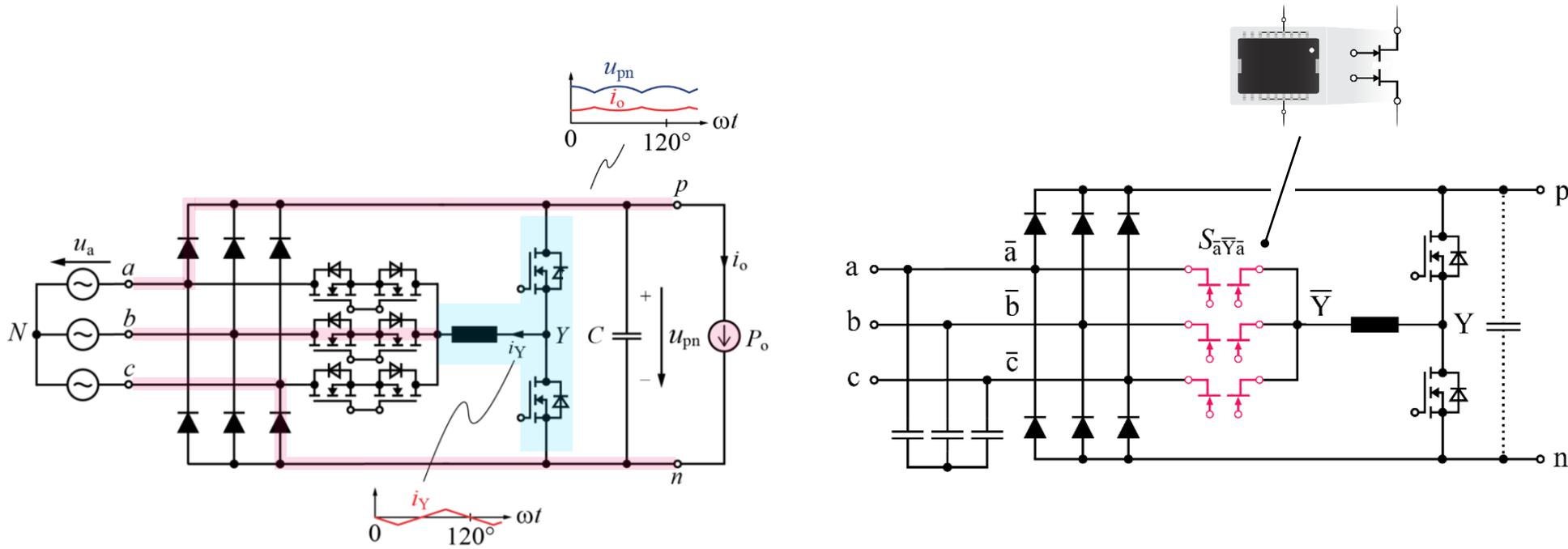
Source: **Panasonic** ideas for life



- **M-BDS** → **Factor of 4 Reduction of Chip Area Comp. to Discrete Realization of Same  $R_{(on)}$  (!)**

# Remark Application of GaN M-BDS (2)

- Realization of the **Phase Selector Switches** of 3<sup>rd</sup> Harmonic Inj. PFC Rectifiers
- **Bipolar Voltage Blocking / Current Carrying Capability**



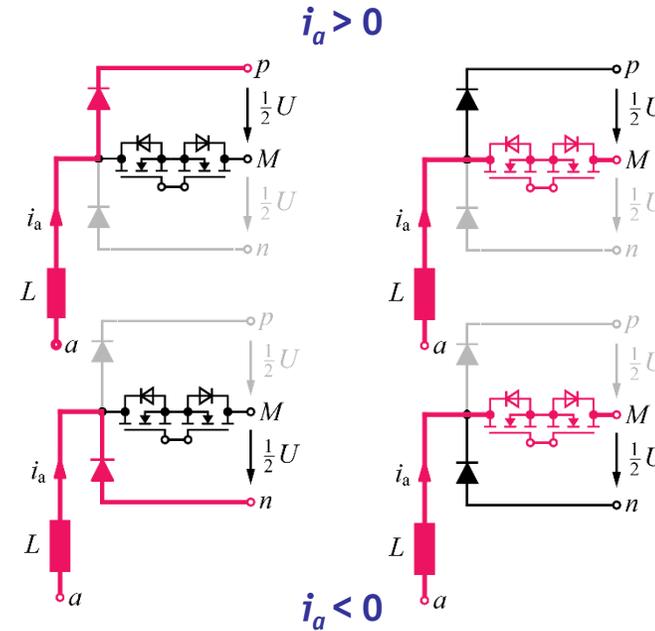
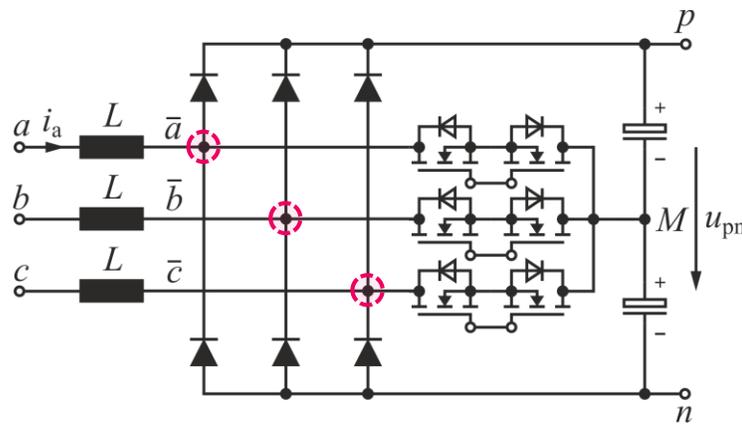
- **M-BDS** → **Factor of 4 Reduction of Chip Area Comp. to Discrete Realization of Same  $R_{(on)}$  (!)**



————— **3-Level T-Type  
PFC Rectifier** —————

# 3-Level T-Type PFC (Vienna) Rectifier

- Control of Diode Bridge Input Voltage → *Sinusoidal Input Current Shaping*
- Controlled Output Voltage > Mains Line-to-Line Voltage Amplitude → *Boost Type*
- *Low Conduction Losses* Compared to Alternative 3-Level Topologies



- Voltage Stress of T-Type Switches Defined by *Half (!) the DC-Link Voltage*

# Vienna Rectifier Demonstrator

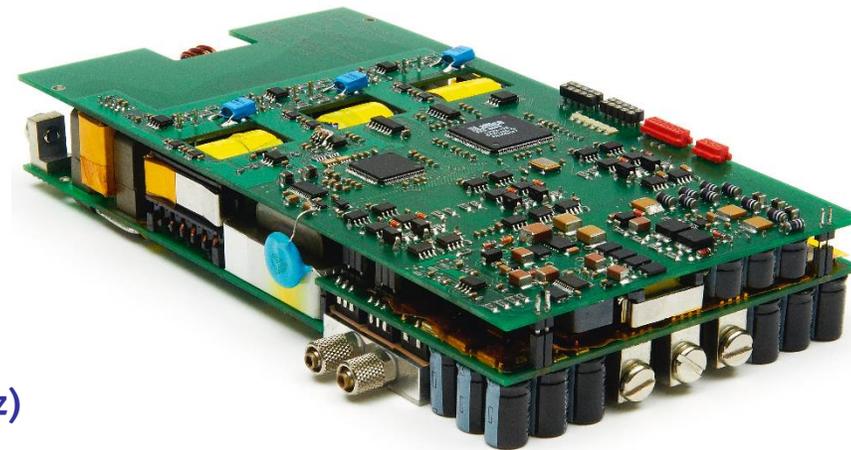
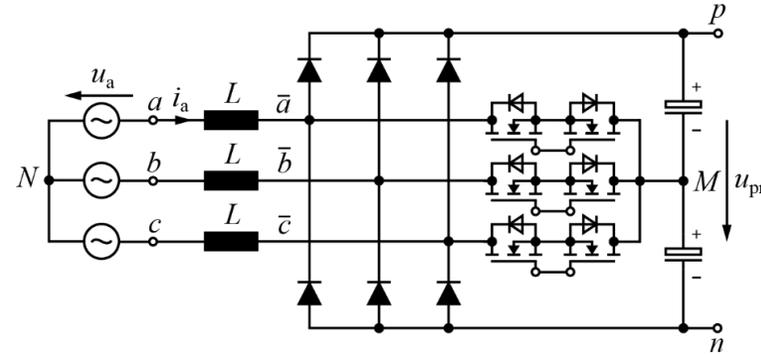
- Design for More Electric Aircraft Application
- 650V CoolMOS & 1200V SiC Diodes
- Coldplate Cooling

$P_o = 10 \text{ kW}$   
 $U_N = 400V_{AC} \pm 10\%$   
 $f_N = 50\text{Hz or } 360 \dots 800\text{Hz}$   
 $U_o = 800V_{DC}$

$\eta = 96.8\%$

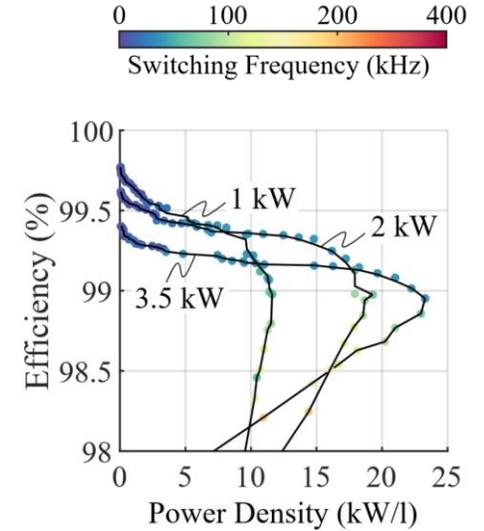
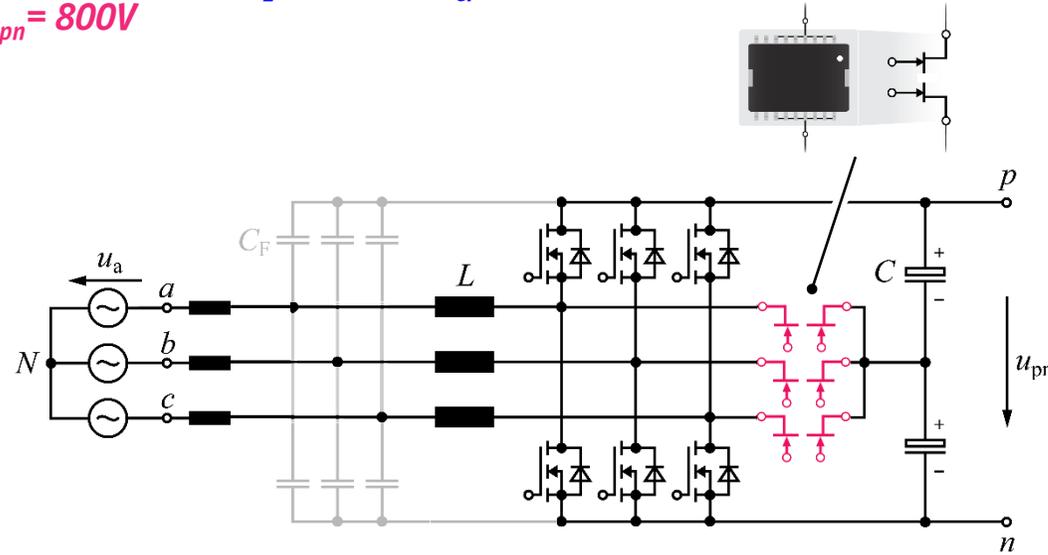
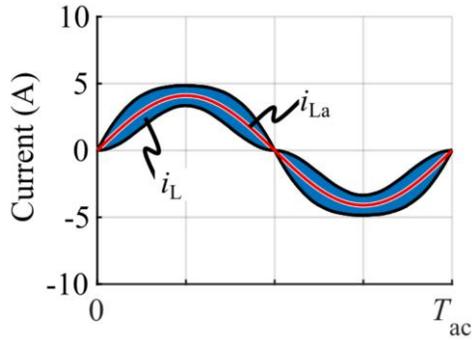
★  $\rho = 10 \text{ kW/dm}^3$

- $THD_i = 1.6\% @ f_N = 800\text{Hz} (f_p = 250\text{kHz})$



# Remark Application of GaN M-BDS

- 600V GaN M-BDSs,  $R_{(on)}=140\text{m}\Omega$
- 1200V SiC MOSFETs,  $R_{(on)}=140\text{m}\Omega$
- Heatsink Design for  $T_j=120^\circ\text{C}$ ,  $\text{CSPI}=15\text{W}/\text{dm}^3\text{K}$
- CCM Operation,  $\Delta i_L=\pm 30\%$ ,  $\Delta u_{CF}=\pm 1\%$
- $U_{pn}=800\text{V}$



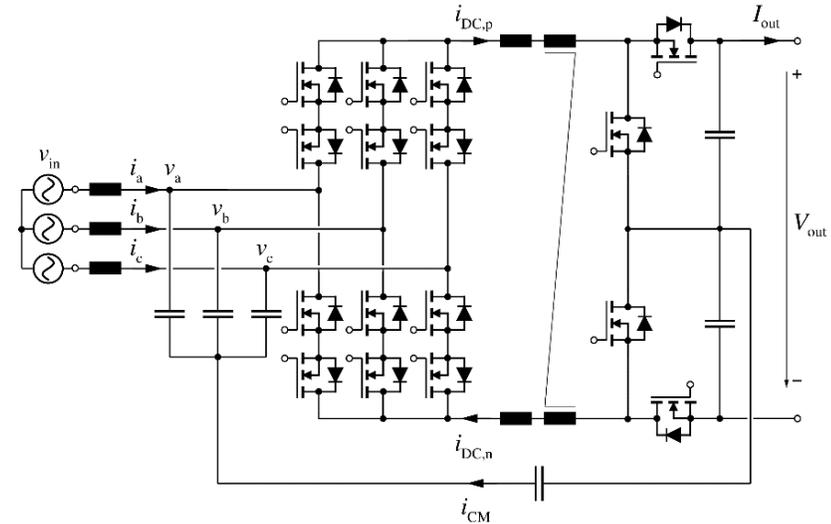
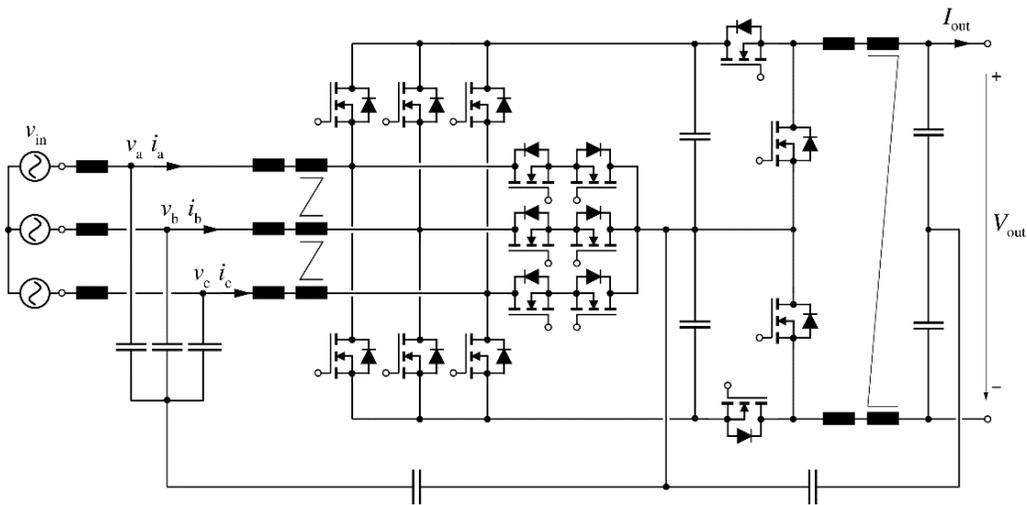
- Bidirectional Power Flow
- Max. Power Density of  $20\text{kW}/\text{dm}^3$  (w/o Full EMI-Filter) @ 99% Efficiency



***Buck-Boost  
Current DC-Link  
PFC Rectifier***

## Bidirectional *Buck-Boost* PFC Rectifier Concepts

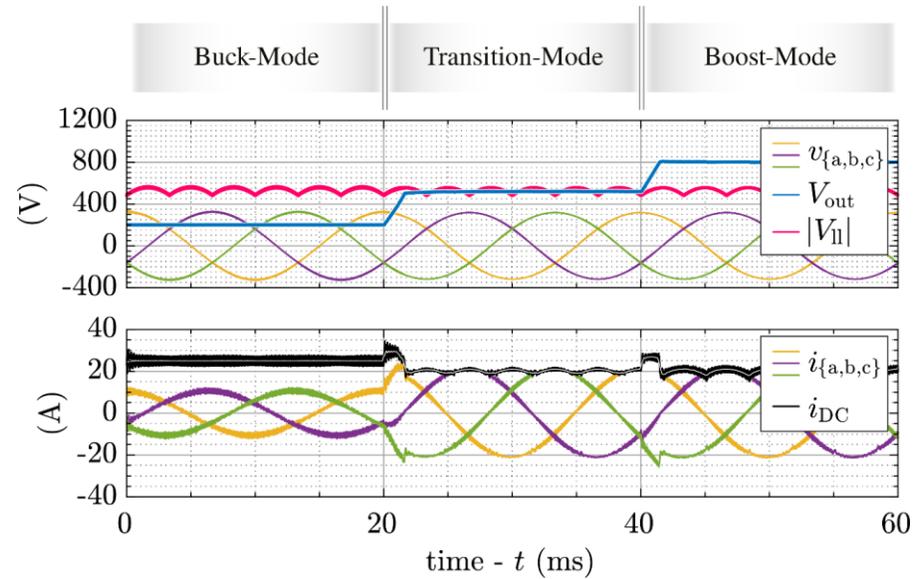
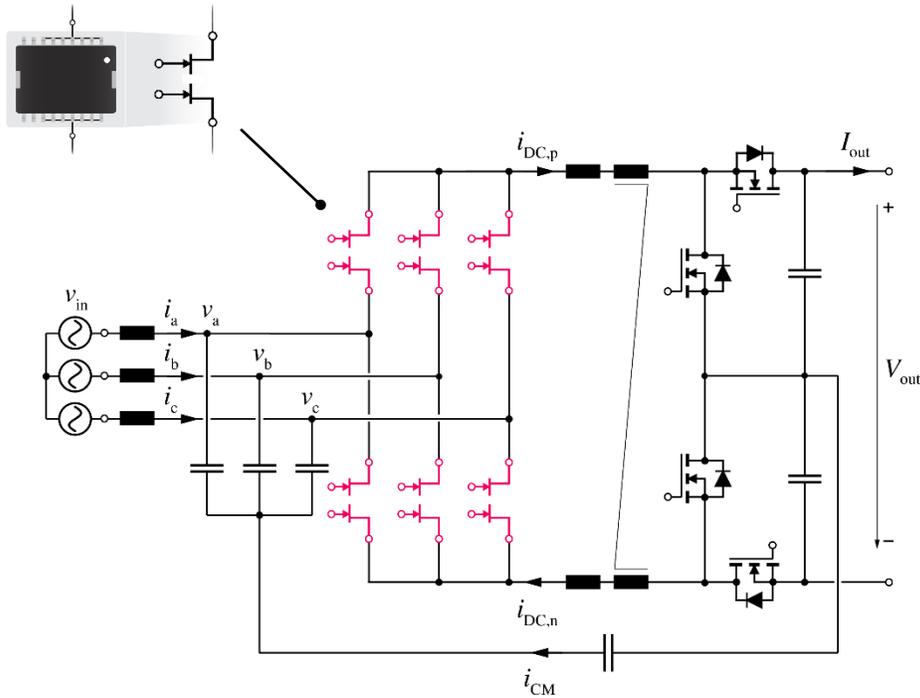
- *Boost—Buck OR Buck—Boost Combination*
- *Closed Loop vs. Open Loop Mains Current Control & Active Input Filter Damping*
- *“Synergetic Control” of AC/DC and DC/DC Converter Stage*



- *AC/DC Buck-Stage Output Inductor Utilized as DC/DC Boost Inductor → Min. # of Inductive Components*

# Remark Application of GaN M-BDS

- **“Synergetic” Control of CSR-Stage & Boost-Stage**
- **6-Pulse-Shaping of  $i_{DC}$  by Boost-Stage → Allows Clamping of a CSR-Phase (2/3 Modulation)**



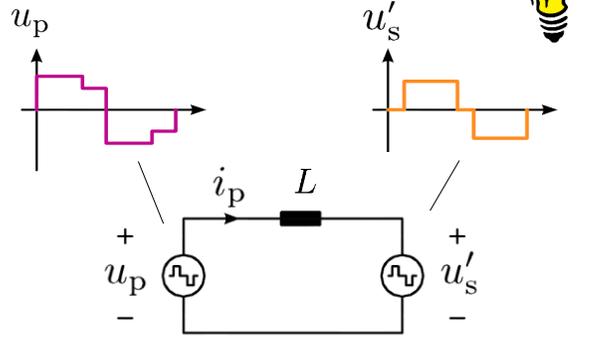
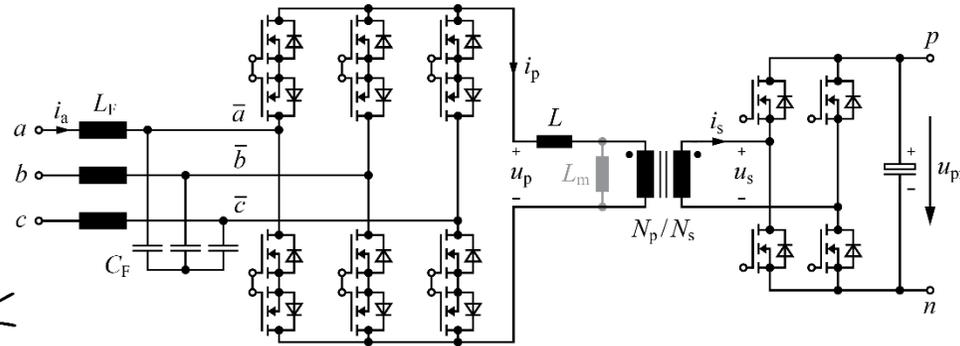
- **Switching of Only 2 of 3 Phase Legs → Significant Red. of Sw. Losses**
- **Seamless Transition from Buck @  $i_{DC}=const.$  to Full Boost Operation @ 6-Pulse  $i_{DC}$**



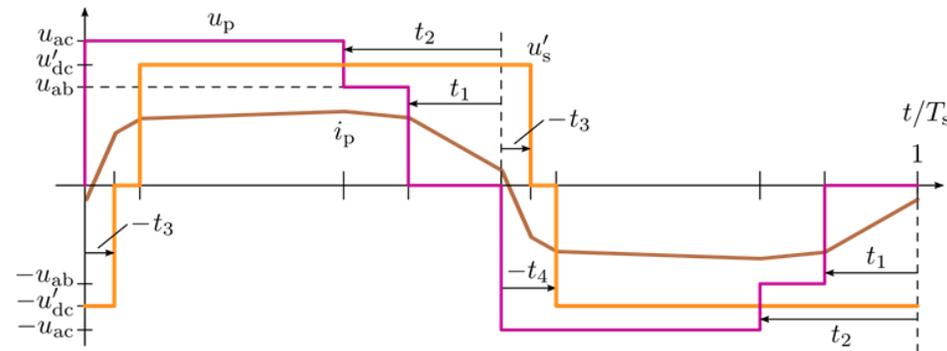
————— *3- $\Phi$  Isolated  
Matrix-Type PFC  
Rectifier* —————

# Isolated Matrix-Type PFC Rectifier (1)

- Based on Dual Active Bridge (DAB) Concept
- Opt. Modulation ( $t_1 \dots t_4$ ) for Min. Transformer RMS Curr. & ZVS or ZCS
- Allows Buck-Boost Operation



• Equivalent Circuit

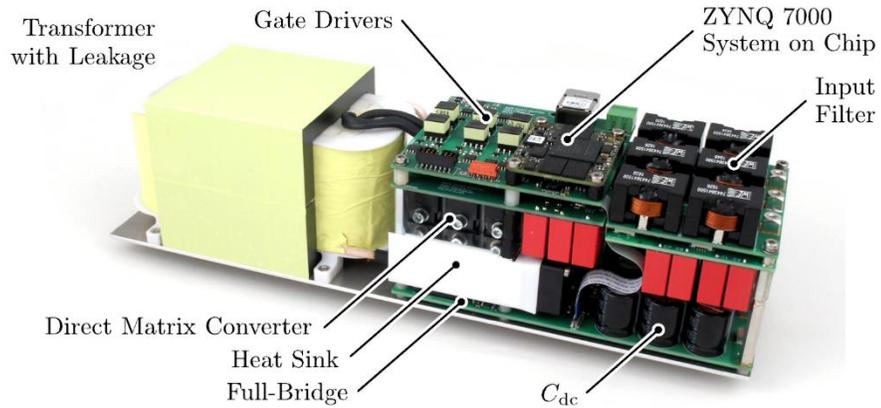


• Transformer Voltages / Currents

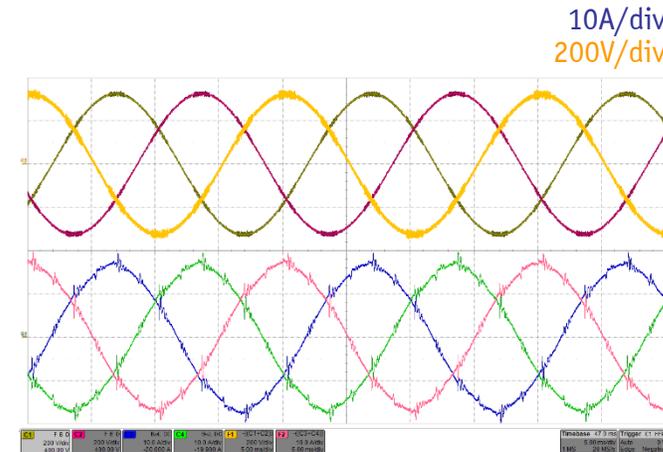
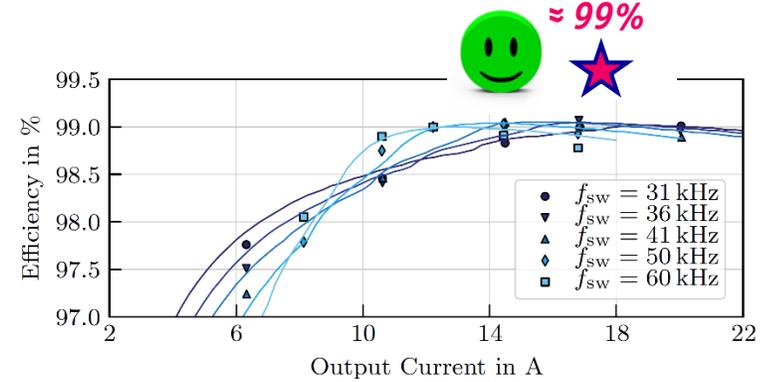
# Isolated Matrix-Type PFC Rectifier (2)

- Efficiency  $\eta = 98.9\%$  @ 60% Rated Load (ZVS)
- Mains Current  $THD_I \approx 4\%$  @ Rated Load
- Power Density  $\rho \approx 4\text{kW}/\text{dm}^3$

$P_o = 8\text{ kW}$   
 $U_N = 400\text{V}_{AC} \rightarrow U_o = 400\text{V}_{DC}$   
 $f_s = 36\text{kHz}$

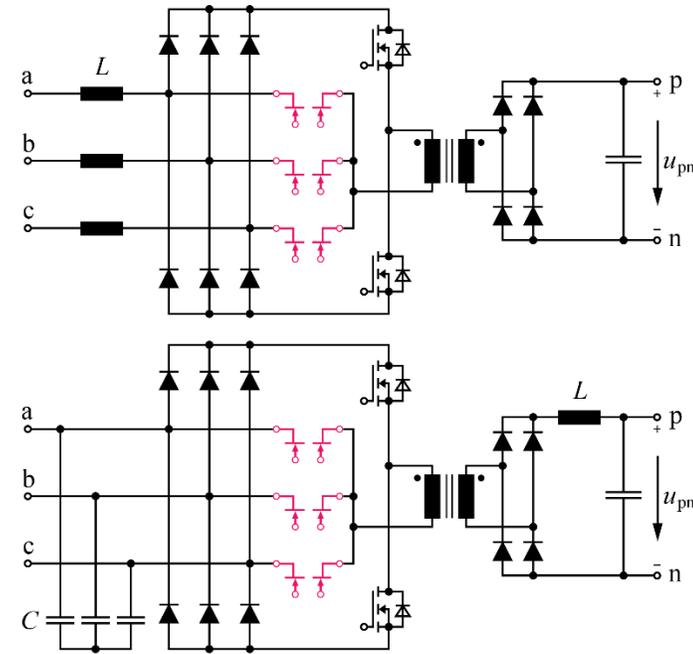
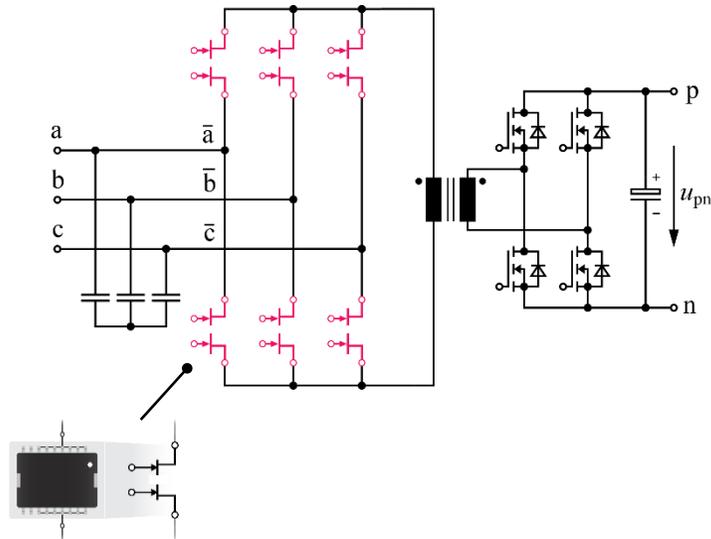


- ▶ 900V / 10m $\Omega$  SiC Power MOSFETs
- ▶ Opt. Modulation Based on 3D Look-Up Table



# Remark Application of GaN M-BDS

- Matrix-Type Bidirectional DAB-Based Topology
- Unidir. Vienna Rectifier II (Boost-Type)
- Unidir. Vienna Rectifier III (Buck-Type)



- *Functional Integration* → *Lower Complexity* BUT *Limited Controllability*

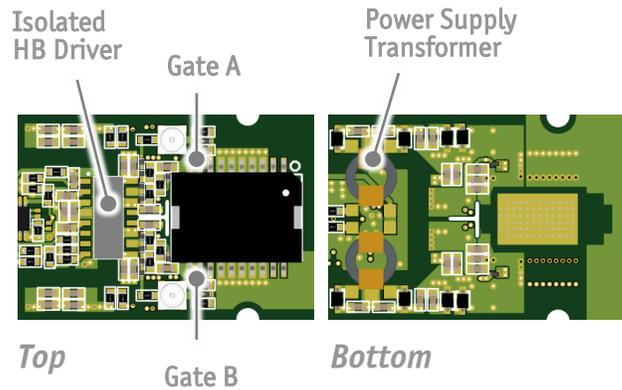


**Outlook**

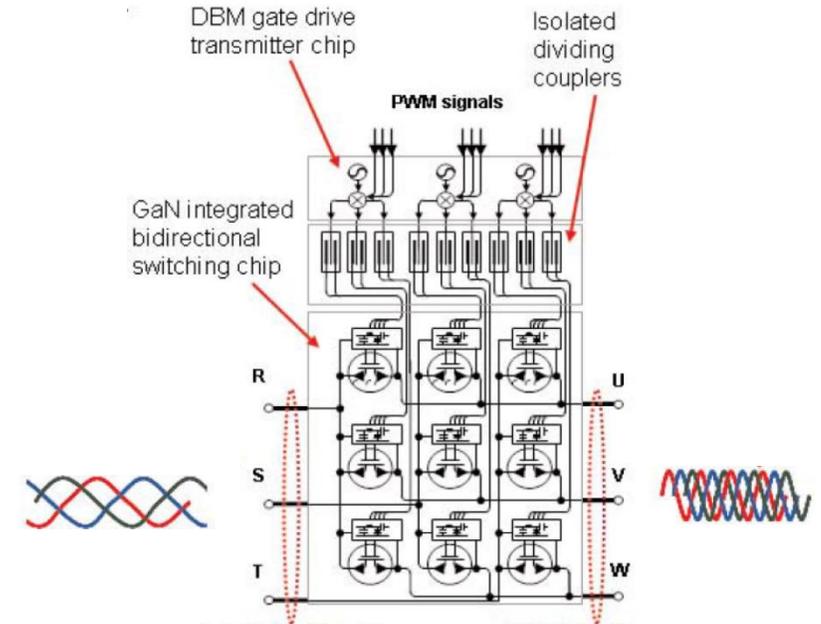
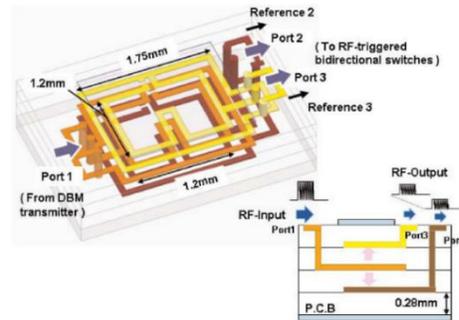
# Monolithic 3D-Integration

Source: **Panasonic** ISSCC 2014

- **M-BDS GaN 3x3 Matrix Converter with Drive-By-Microwave (DBM) Technology**
- **9 Dual-Gate GaN AC-Switches / 4-Step Commutation**
- **DBM Gate Drive Transmitter Chip & Isolating Couplers**
- **Ultra Compact → 25 x 18 mm<sup>2</sup> (600V, 10A – 5kW Motor)**



5.0GHz Isolated (5kV<sub>DC</sub>) Dividing Coupler



- **Massive Space Saving Compared to Discrete Realization (!)**

**Thank you!**

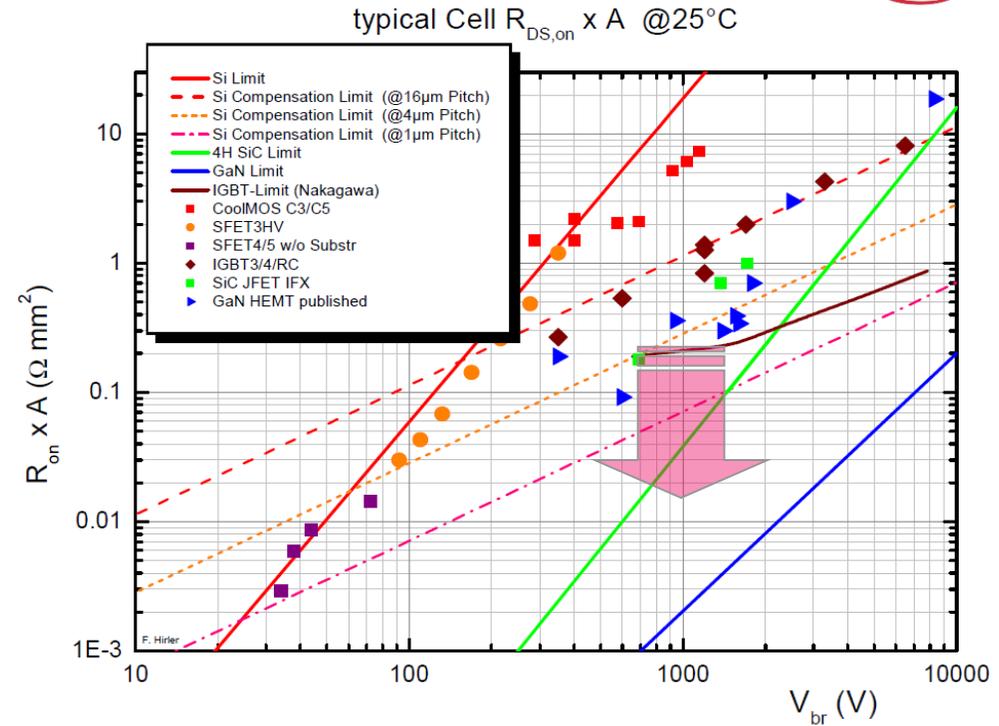




# Technology Push — WBG Power Semiconductors

- Higher Critical E-Field Compared to Si → Thinner Drift Layer
- Low  $R_{DS(on)}$  High-Voltage Unipolar Devices / Small Chip Size
- Higher Max. Junction Temperature  $T_{j,max}$
- Excellent Switching Performance

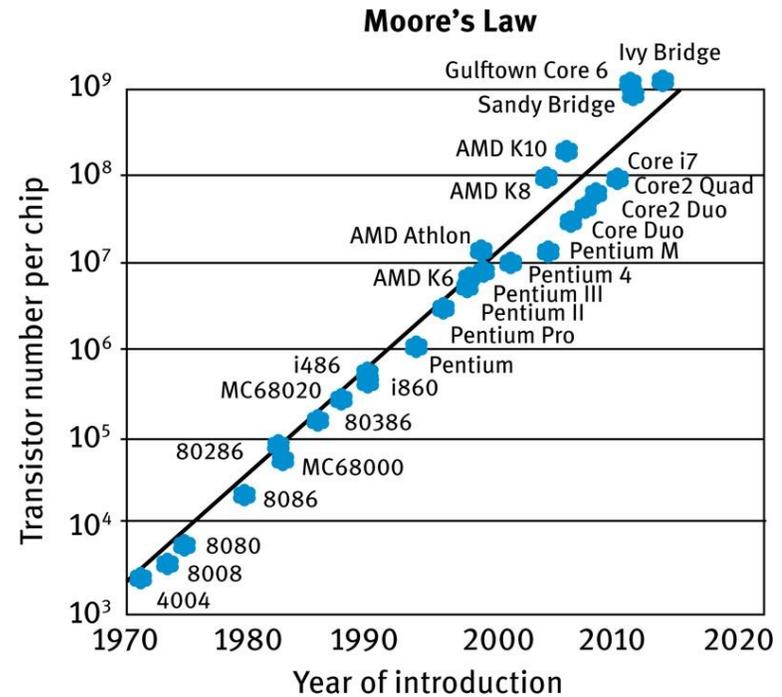
Source: 



- Advanced Packaging Mandatory (!)

# Technology Push — Digitalization

- **Exponentially Improving uC / Storage Technology (!)**
- Extreme Levels of Density / Processing Speed
- Software Defined Functions / Flexibility
- Cont. Relative Cost Reduction



Source: Ostendorf & König / DeGruyter

- Fully Digital Control of Complex Multi-Switch Systems
- Massive Computational Power → Fully Automated Design & Manufacturing / Industrial IoT (IIoT)



 **End**